

SPECIAL ISSUE ON ATOMIC LAYER DEPOSITION (ALD)

Dielectric barrier characteristics of Si-rich silicon nitride films deposited by plasma enhanced atomic layer deposition

Hwanwoo Kim, Hyoseok Song, Changhee Shin, Kangsoo Kim, Woochool Jang, Hyunjung Kim, Seokyeon Shin and Hyeongtag Jeon
J. Vac. Sci. Technol. A **35**, 01A101 (2017);
<http://dx.doi.org/10.1116/1.4964889>

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Quasi-atomic layer etching of silicon nitride

Sonam D. Sherpa and Alok Ranjan
J. Vac. Sci. Technol. A **35**, 01A102 (2017);
<http://dx.doi.org/10.1116/1.4967236>

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Anomalously high alumina atomic layer deposition growth per cycle during trimethylaluminum under- dosing conditions

Hossein Salami, Andrew Poissant and Raymond A. Adomaitis
J. Vac. Sci. Technol. A **35**, 01B101 (2017);
<http://dx.doi.org/10.1116/1.4963368>

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Mechanistic modeling study of atomic layer deposition process optimization in a fluidized bed reactor

Chen-Long Duan, Peng-Hui Zhu, Zhang Deng, Yun Li, Bin Shan, Hai-Sheng Fang, Guang Feng and Rong Chen
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Investigating routes toward atomic layer deposition of silicon carbide: *Ab initio* screening of potential silicon and carbon precursors

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Selective deposition of Ta₂O₅ by adding plasma etching super-cycles in plasma enhanced atomic layer deposition steps

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<http://dx.doi.org/10.1116/1.4965966>

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Aluminum oxide/titanium dioxide nanolaminates grown by atomic layer deposition: Growth and mechanical properties

Oili M. E. Ylivaara, Lauri Kilpi, Xuwen Liu, Sakari Sintonen, Saima Ali, Mikko Laitinen, Jaakko Julin, Eero Haimi, Timo Sajavaara, Harri Lipsanen, Simo-Pekka Hannula, Helena Ronkainen and Riikka L. Puurunen
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Effects of GaSb surface preparation on the characteristics of HfO₂/Al₂O₃/GaSb metal-oxide-semiconductor capacitors prepared by atomic layer deposition

Wei-Jen Hsueh, Cheng-Yu Chen, Chao-Min Chang, Jen-Inn Chyi and Mao-Lin Huang
J. Vac. Sci. Technol. A **35**, 01B106 (2017);
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Deposition of an organic–inorganic hybrid material onto carbon fibers via the introduction of furfuryl alcohol into the atomic layer deposition process of titania and subsequent pyrolysis

Christian Militzer, Stefan Knohl, Volodymyr Dzhagan, Dietrich R. T. Zahn and Werner A. Goedel
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Tunable optical properties in atomic layer deposition grown ZnO thin films

Dipayan Pal, Aakash Mathur, Ajaib Singh, Jaya Singhal, Amartya Sengupta, Surjendu Dutta, Stefan Zollner and Sudeshna Chattopadhyay
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Vapor deposition of copper(I) bromide films via a two-step conversion process

Rachel Heasley, Christina M. Chang, Luke M. Davis, Kathy Liu and Roy G. Gordon
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<http://dx.doi.org/10.1116/1.4967726>

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Characterization of Al₂O₃ and ZnO multilayer thin films deposited by low temperature thermal atomic layer deposition on transparent polyimide

Seung Hak Song, Myoung Youb Lee, Gyeong Beom Lee and Byoung-Ho Choi
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